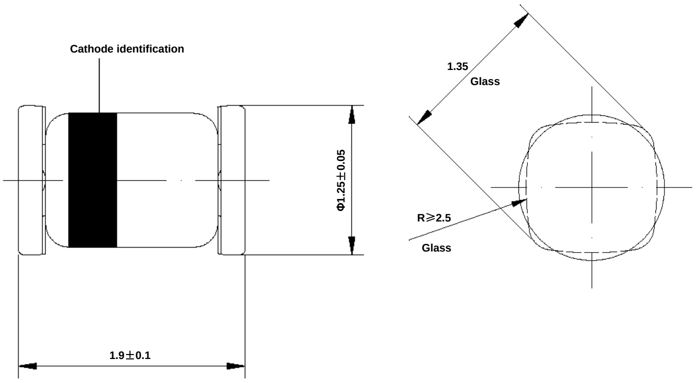
BZM55B Series

Zener Diodes

V_Z : 2.0 - 100 Volts
P_D : 500 mWatts

MICRO MELF



Glass Case
Micro Melf

Features

1. Saving space
2. Fits onto SOD 323/SOT 23 footprints
3. Micro Melf package

Applications

Voltage stabilization

Absolute Maximum Ratings

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Value	Unit
Power dissipation	R_{thJA}≦300K/W		P_V	500	mW
Z-current			I_Z	P_V/V_Z	mA
Junction temperature			T_j	175	℃
Storage temperature range			T_{stg}	-65~+175	℃

Maximum Thermal Resistance

T_j=25℃

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm×50mm×1.6mm	R_{thJA}	500	K/W

Stresses exceeding maximum ratings may damage the device. Maximum ratings are stress ratings only. Functional operation above the recommended operating conditions is not implied. Extended exposure to stresses above the recommended operating conditions may affect device reliability.

Electrical Characteristics

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=200mA		V_F			1.5	V

Type	V_{Znom}	I_{ZT}	for V_{ZT} and	r_{zjT}	r_{zjK} at	I_{ZK}	I_R and	I_R at	V_R	TK_{VZ}
BZM55B.	V	mA	V	Ω	Ω	mA	μA	μA1)	V	%/K
2V0	2.0	5	1.96~2.04	100	<600	1	<150	<300	1	-0.09~-0.06
2V2	2.2	5	2.16~2.24	100	<600	1	<150	<300	1	-0.09~-0.06
2V4	2.4	5	2.35~2.45	<85	<600	1	<50	<100	1	-0.09~-0.06
2V7	2.7	5	2.64~2.76	<85	<600	1	<10	<50	1	-0.09~-0.06
3V0	3.0	5	2.94~3.06	<85	<600	1	<4	<40	1	-0.08~-0.05
3V3	3.3	5	3.24~3.36	<85	<600	1	<2	<40	1	-0.08~-0.05
3V6	3.6	5	3.52~3.36	<85	<600	1	<2	<40	1	-0.08~-0.05
3V9	3.9	5	3.82~3.98	<85	<600	1	<2	<40	1	-0.08~-0.05
4V3	4.3	5	4.22~4.38	<75	<600	1	<1	<20	1	-0.06~-0.03
4V7	4.7	5	4.60~4.80	<60	<600	1	<0.5	<10	1	-0.05~+0.02
5V1	5.1	5	5.00~5.20	<35	<550	1	<0.1	<2	1	-0.02~+0.02
5V6	5.6	5	5.48~5.72	<25	<450	1	<0.1	<2	1	-0.05~+0.05
6V2	6.2	5	6.08~6.32	<10	<200	1	<0.1	<2	2	0.03~0.06
6V8	6.8	5	6.66~6.94	<8	<150	1	<0.1	<2	3	0.03~0.07
7V5	7.5	5	7.35~7.65	<7	<50	1	<0.1	<2	5	0.03~0.07
8V2	8.2	5	8.04~8.36	<7	<50	1	<0.1	<2	6.2	0.03~0.08
9V1	9.1	5	8.92~9.28	<10	<50	1	<0.1	<2	6.8	0.03~0.09
10	10	5	9.80~10.20	<15	<70	1	<0.1	<2	7.5	0.03~0.1
11	11	5	10.78~11.22	<20	<70	1	<0.1	<2	8.2	0.03~0.11
12	12	5	11.76~12.24	<20	<90	1	<0.1	<2	9.1	0.03~0.11
13	13	5	12.74~13.26	<26	<110	1	<0.1	<2	10	0.03~0.11
15	15	5	14.70~15.30	<30	<110	1	<0.1	<2	11	0.03~0.11
16	16	5	15.70~16.30	<40	<170	1	<0.1	<2	12	0.03~0.11
18	18	5	17.64~18.36	<50	<170	1	<0.1	<2	13	0.03~0.11
20	20	5	19.60~20.40	<55	<220	1	<0.1	<2	15	0.03~0.11
22	22	5	21.55~22.45	<55	<220	1	<0.1	<2	16	0.04~0.12
24	24	5	23.5~24.5	<80	<220	1	<0.1	<2	18	0.04~0.12
27	27	5	26.4~27.6	<80	<220	1	<0.1	<2	20	0.04~0.12
30	30	5	29.4~30.6	<80	<220	1	<0.1	<2	22	0.04~0.12
33	33	5	32.4~33.6	<80	<220	1	<0.1	<2	24	0.04~0.12
36	36	5	35.3~36.7	<80	<220	1	<0.1	<2	27	0.04~0.12
39	39	2.5	38.2~39.8	<90	<500	0.5	<0.1	<5	30	0.04~0.12
43	43	2.5	42.1~43.9	<90	<600	0.5	<0.1	<5	33	0.04~0.12
47	47	2.5	46.1~47.9	<110	<700	0.5	<0.1	<5	36	0.04~0.12
51	51	2.5	50.0~52.0	<125	<700	0.5	<0.1	<10	39	0.04~0.12
56	56	2.5	54.9~57.1	<135	<1000	0.5	<0.1	<10	43	0.04~0.12
62	62	2.5	60.8~63.2	<150	<1000	0.5	<0.1	<10	47	0.04~0.12
68	68	2.5	66.6~69.4	<200	<1000	0.5	<0.1	<10	51	0.04~0.12
75	75	2.5	73.5~76.5	<250	<1500	0.5	<0.1	<10	56	0.04~0.12
82	82	2.5	80.4~83.6	<300	<2000	0.5	<0.1	<10	62	0.04~0.12
91	91	1.0	89.2~92.8	<450	<5000	0.1	<0.1	<10	68	0.04~0.12
100	100	1.0	98~102	<450	<5000	0.1	<0.1	<10	75	0.04~0.12

1) at T_j=150℃

Characteristics (T$_j$=25℃ unless otherwise specified)

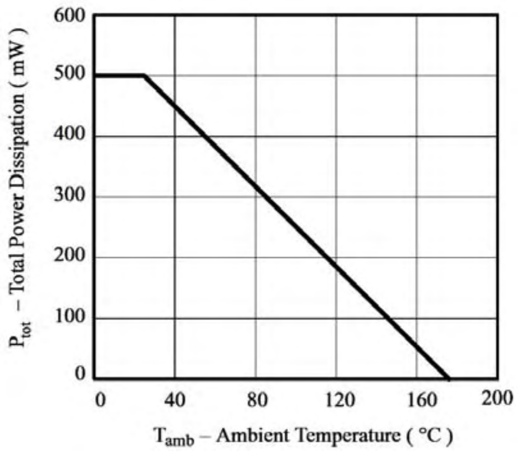


Figure 1. Total Power Dissipation vs. Ambient Temperature

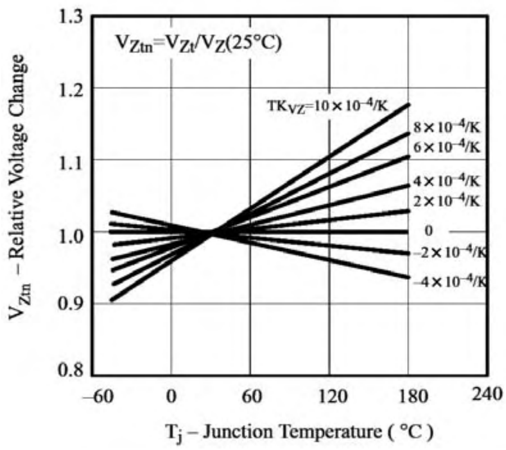


Figure 4. Typical Change of Working Voltage Vs. Junction Temperature

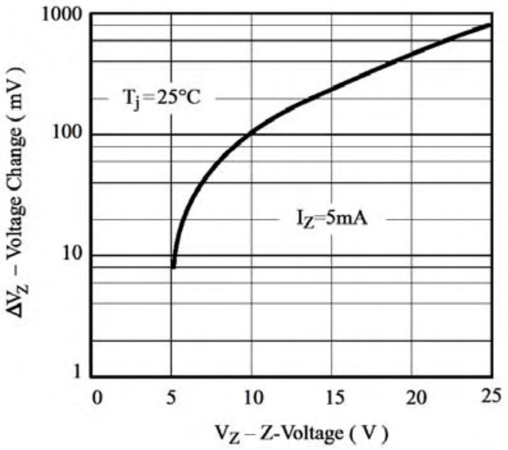


Figure 2. Typical Change of Working Voltage under Operating Conditions at T$_{amb}$=25℃

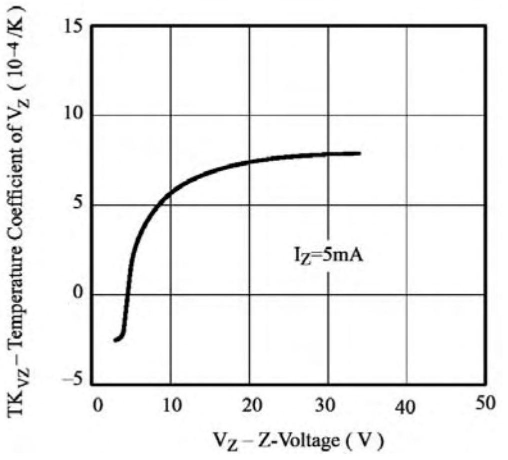


Figure 5. Temperature Coefficient of Vz vs. Z-Voltage

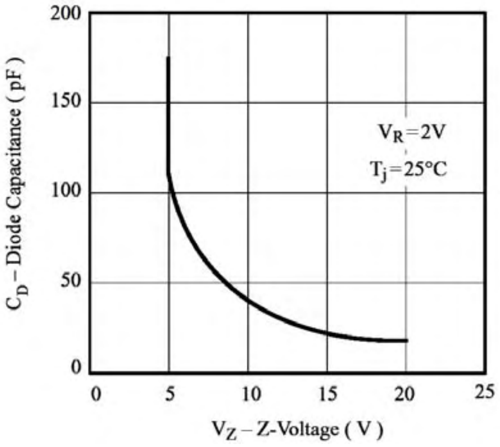


Figure 3. Diode Capacitance vs. Z-voltage

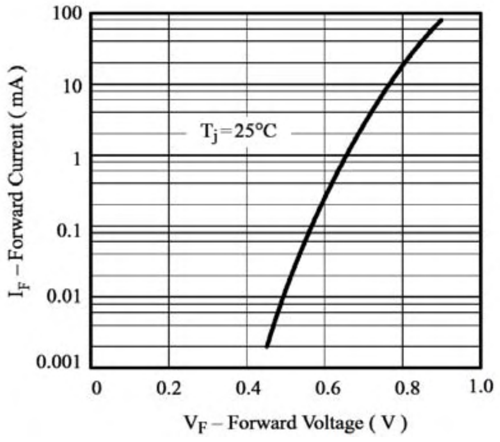


Figure 6. Forward Current vs. Forward Voltage

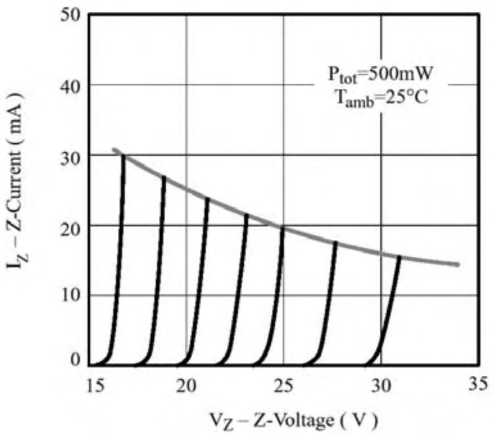


Figure 8. Z-Current vs. Z-Voltage

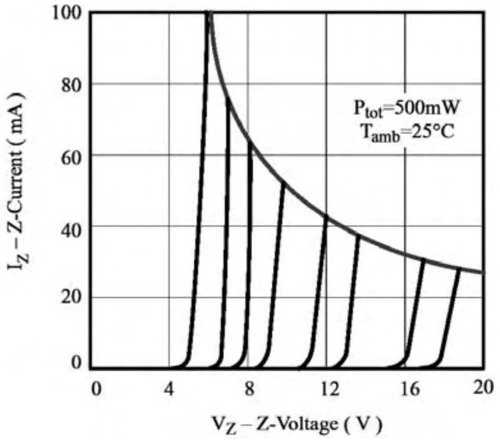


Figure 7. Z-Current vs. Z-Voltage

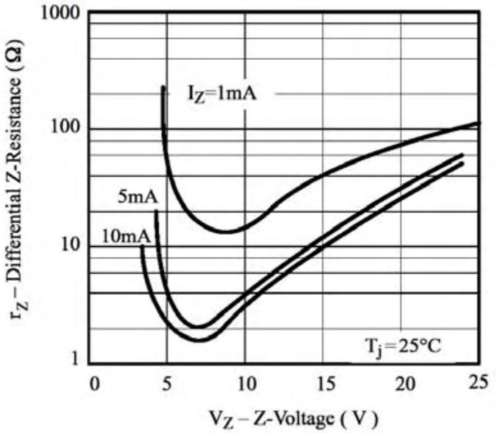


Figure 9. Differential Z-Resistance Vz vs. Z-Voltage

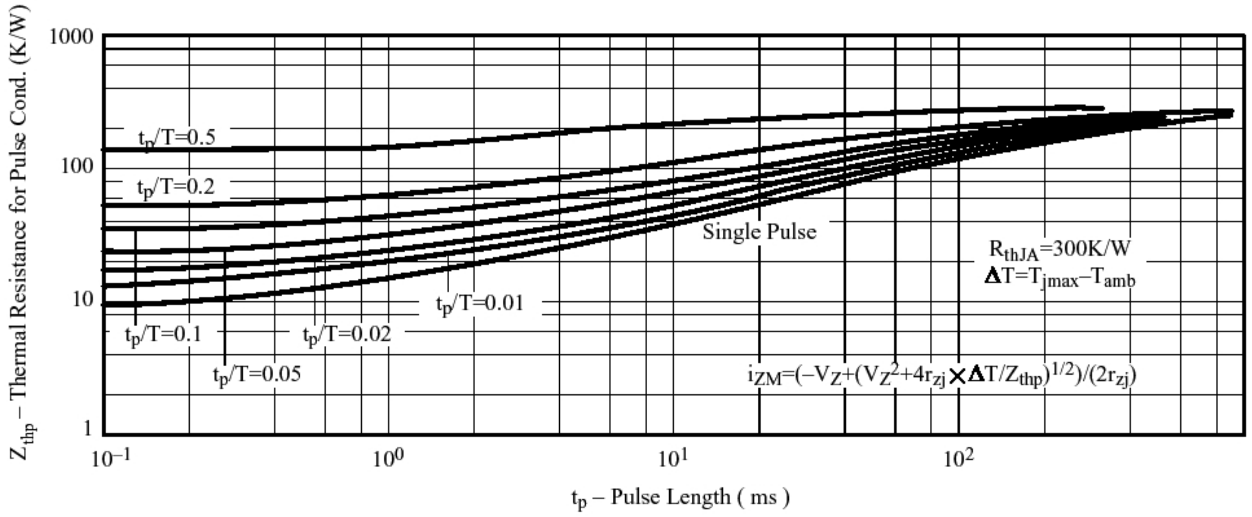


Figure 10. Thermal Response